	L#	Hits	Search Text	DBs	Time Stamp
1	L1	476231	(anneal\$3 heat\$3 bak\$3) same (HCI or hydrochloric or hydrofluoric or hydrobromic or hydroiodic or HBr or HF or HI or chlorine or fluorine or bromine or iodine or halogen or "CI.sub.2" "Br.sub.2" "F.sub.2" "I.sub.2" or cl br f i)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	11:30
2	L8	162793	(treat\$4 pretreat\$ condition\$3 precondition\$3 prepar\$3 smooth\$3 roughness) same 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	11:23
3	L15	11414	8 same (silicon or semiconductor or si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
4	L22	263688	(anneal\$3 heat\$3 bak\$3) with (HCI or hydrochloric or hydrofluoric or hydrobromic or hydroiodic or HBr or HF or HI or chlorine or fluorine or bromine or iodine or halogen or "CI.sub.2" "Br.sub.2" "F.sub.2" "I.sub.2" or cl br f i)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	11:24
5	L29	73880	22 same (treat\$4 pretreat\$ condition\$3 precondition\$3 prepar\$3 smooth\$3 roughness)	JPO; DERWENT; IBM_TDB	11:52
6	L36	49120	epitax\$5 near25 (si silicon semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	11:25
7	L43	5176	29 same (silicon or semiconductor or si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	12:08
8	L57	432	36 and 43	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	11:53
9	L64	370	57 and @ad<19990421	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	11:54
10	L71	122	57 and @rlad<19990421	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	11:54
11	L78	381	64 71	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
12	L85	172356	(anneal\$3 heat\$3 bak\$3) same (HCl or hydrochloric or hydrofluoric or hydrobromic or hydroiodic or HBr or HF or HI or chlorine or fluorine or bromine or iodine or halogen or "Cl.sub.2" "Br.sub.2" "F.sub.2" "I.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
13	L92	80697	(anneal\$3 heat\$3 bak\$3) with (HCl or hydrochloric or hydrofluoric or hydrobromic or hydroiodic or HBr or HF or HI or chlorine or fluorine or bromine or iodine or halogen or "Cl.sub.2" "Br.sub.2" "F.sub.2" "I.sub.2")	JPO; DERWENT; IBM_TDB	11:32
14	L99	25079	92 same (treat\$4 pretreat\$ condition\$3 precondition\$3 prepar\$3 smooth\$3 roughness)	JPO; DERWENT; IBM_TDB	11:53
15	L106	363	36 and 99	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
16	L113	313	106 and @ad<19990421	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	11:54
17	L120	110	106 and @rlad<19990421	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
18	L127	321	113 120	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
19	L134	168693	(anneal\$3 heat\$3 bak\$3) same (HCl or hydrochloric or hydrofluoric or hydrobromic or hydroiodic or HBr or HF or HI or chlorine or fluorine or bromine or iodine or (halogen not adj lamp) or "Cl.sub.2" "Br.sub.2" "F.sub.2" "I.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/06 12:05
20	L141	27524	134 same ("H.sub.2" or hydrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	12:06
21	L148	2860	141 same (silicon or semiconductor or si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	12:08
22	L155	721	148 and @rlad<19990421	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	

	L#	Hits	Search Text	DBs	Time Stamp
23 [°]	L162		148 and @ad<19990421	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	12:09
24	ļ	2593	155 162	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/06 12:09
25	L176	531	36 and 169	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	14:33
26	L183	285	(Goesele or bruel).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/06 14:33
27	L190	10	183 and 36	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	14:38
28	L197	15949	(cleav\$3 split\$4 detach\$4 separat\$4) and 36	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	14:40
29	L204	489	(cleav\$3 split\$4 detach\$4) same 36	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	14:40
30	L211	187	(cleav\$3 split\$4 detach\$4) near20 36	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDE	2002/03/06 14:41